

### BAS16T/BAW56T/BAV70T/BAV99T

SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 150 mW ( $T_{amb}=25^\circ C$ )

Forward Current

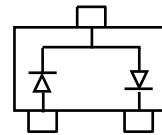
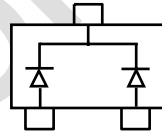
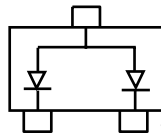
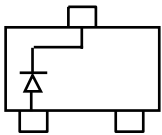
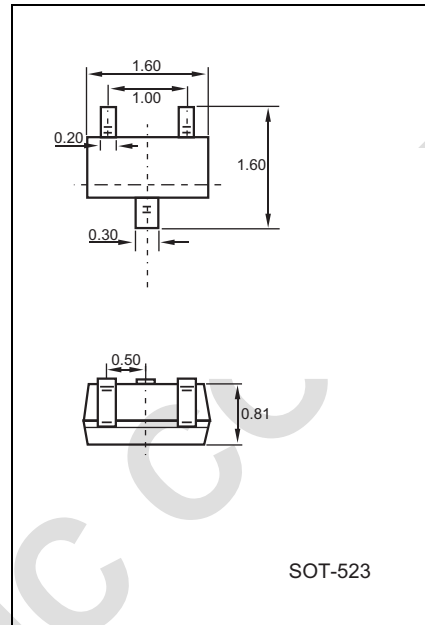
$I_F$ : 75 mA

Reverse Voltage

$V_R$ : 85 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ C$  to  $+150^\circ C$



BAS16T Marking: A2

BAW56T Marking: JD

BAV70T Marking: JJ

BAV99T Marking: JE

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	85		V
Reverse voltage leakage current	$I_{R1}$	$V_R=75V$		2	$\mu A$
	$I_{R2}$	$V_R=25V$		0.03	$\mu A$
Forward voltage	$V_F$	$I_F=1mA$		715	mV
		$I_F=10mA$		855	
		$I_F=50mA$		1000	
		$I_F=150mA$		1250	
Diode capacitance	$C_D$	$V_R=0V, f=1MHz$		1.5	pF
Reverse recovery time	$t_{rr}$			4	nS

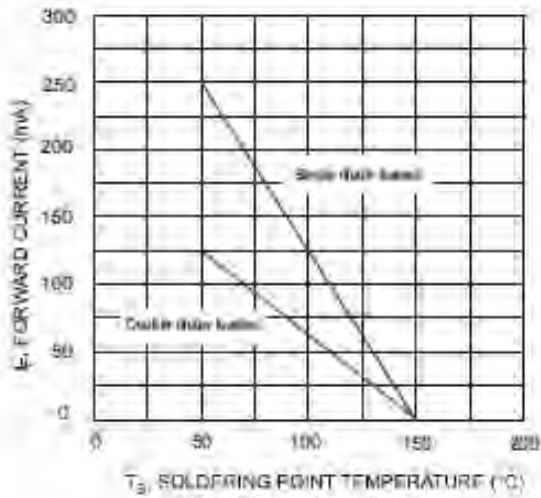


Fig. 1. Current Degrading Curve

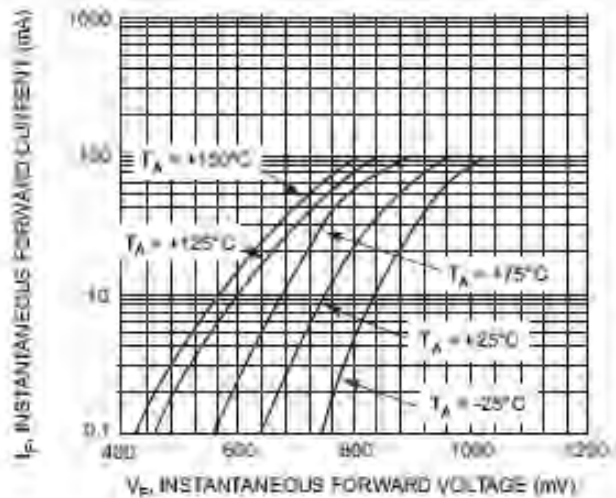


Fig. 2. Typical Forward Characteristics

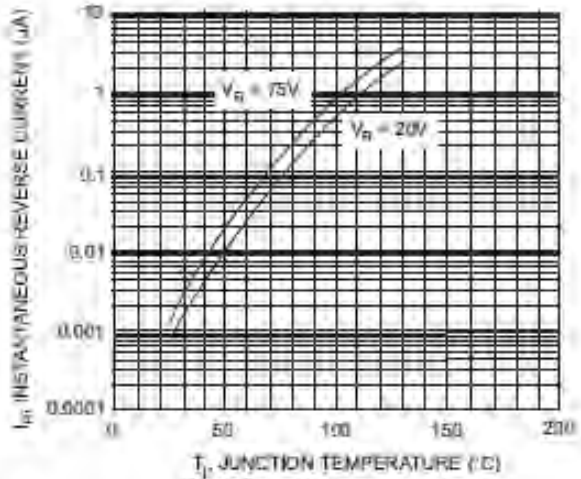


Fig. 3. Typical Reverse Characteristics